ASSP for Power Supply Applications (Secondary battery)

# DC/DC Converter IC for Charging Li-ion Battery

# MB39A125/126

### DESCRIPTION

MB39A125/126 is a DC/DC converter IC for charging Li-ion battery, which is suitable for down-conversion, and uses pulse width modulation (PWM) for controlling the output voltage and current independently. This IC integrates the build-in comparator for the voltage detection of the AC adapter, and selects the AC adapter or battery automatically for power supply to the system.

Provides a wide range of power supply voltage, low standby current, and high efficiency, which makes them ideal as a built-in charging device in products such as notebook PC.

### ■ FEATURES

- High efficiency : 97% (MAX)
- · Built-in two constant current control circuits
- Analog control of the charging current value (+INE1, +INE2 terminal)
- Built-in AC adapter voltage detection function (ACOK, XACOK terminal)

(Continued)



# FUJITSU

#### PACKAGES

#### (Continued)

- External output voltage setting resistor : MB39A125
- Built-in output voltage setting resistor : MB39A126
- Built-in charge stop function at low VCC
- Output voltage setting accuracy :  $\pm$  0.74% (Ta = -10 °C to +85 °C) : MB39A125

: 12.6 V/16.8 V ± 0.8% (Ta = -10 °C to +85 °C) : MB39A126

• Built-in high accuracy current detection amplifier ( $\pm 5\%$ ) (At input voltage difference 100 mV) ,

(±15%) (At input voltage difference 20 mV)

- In IC standby mode (Icc = 0 µA Typ), make output voltage setting resistor open to prevent inefficient current loss
- Built-in soft-start circuit
- Standby current : 0  $\mu$ A (Typ)
- Totem-pole type output for Pch MOS FET

#### ■ PIN ASSIGNMENTS

#### • MB39A125













### ■ PIN DESCRIPTIONS

#### • MB39A125 : SSOP-24

Pin No.	Pin Name	I/O	Description			
1	-INC2	I	Current detection amplifier (Current Amp2) inverted input terminal			
2	OUTC2	0	Current detection amplifier (Current Amp2) output terminal			
3	+INE2	I	Error amplifier (Error Amp2) non-inverted input terminal			
4	-INE2	I	Error amplifier (Error Amp2) inverted input terminal			
5	ACOK	0	AC adapter voltage detection block (AC Comp.) output terminal ACOK = L when ACIN = H, ACOK = Hi-Z when ACIN = L, ACOK = Hi-Z when CTL = L			
6	VREF	0	Reference voltage output terminal			
7	ACIN	I	AC adapter voltage detection block (AC Comp.) input terminal			
8	–INE1	I	Error amplifier (Error Amp1) inverted input terminal			
9	+INE1	I	Error amplifier (Error Amp1) non-inverted input terminal			
10	OUTC1	0	Current detection amplifier (Current Amp1) output terminal			
11	OUTD	0	When IC is standby mode, this terminal is set to "Hi-Z" to prevent lo of inefficient current through the output voltage setting resistor. Set CTL terminal to "H" level to output "L" level.			
12	-INC1	I	Current detection amplifier (Current Amp1) inverted input terminal			
13	+INC1	I	Current detection amplifier (Current Amp1) non-inverted input terminal			
14	CTL	Ι	Power supply control terminal Setting the CTL terminal at "L" level places the IC in the standby mode.			
15	FB123	0	Error amplifier (Error Amp1, 2, 3) output terminal			
16	–INE3	I	Error amplifier (Error Amp3) inverted input terminal			
17	RT		Triangular wave oscillation frequency setting resistor connection terminal			
18	ХАСОК	0	AC adapter voltage detection block ( AC Comp.) output terminal XACOK = Hi-Z when ACIN = H, XACOK = L when ACIN = L, XACOK = Hi-Z when CTL = L			
19	VH	0	Power supply terminal for FET drive circuit (VH = VCC $- 6$ V)			
20	OUT	0	External FET gate drive terminal			
21	VCC		Power supply terminal for reference voltage, control circuit, and output circuit			
22	CS	_	Soft-start setting capacitor connection terminal			
23	GND		Ground terminal			
24	+INC2	I	Current detection amplifier (Current Amp2) non-inverted input terminal			

#### • MB39A125 : QFN-28

Pin No.	Pin Name	I/O	Description			
1	N.C.		No connection			
2	GND		Ground terminal			
3	+INC2	I	Current detection amplifier (Current Amp2) non-inverted input terminal			
4	N.C.		No connection			
5	-INC2	I	Current detection amplifier (Current Amp2) inverted input terminal			
6	OUTC2	0	Current detection amplifier (Current Amp2) output terminal			
7	+INE2	I	Error amplifier (Error Amp2) non-inverted input terminal			
8	-INE2	I	Error amplifier (Error Amp2) inverted input terminal			
9	ACOK	ο	AC adapter voltage detection block (AC Comp.) output terminal ACOK = L when ACIN = H, ACOK = Hi-Z when ACIN = L, ACOK = Hi-Z when CTL = L			
10	VREF	0	Reference voltage output terminal			
11	ACIN	I	AC adapter voltage detection block (AC Comp.) input terminal			
12	–INE1	I	Error amplifier (Error Amp1) inverted input terminal			
13	+INE1	I	Error amplifier (Error Amp1) non-inverted input terminal			
14	OUTC1	0	Current detection amplifier (Current Amp1) output terminal			
15	N.C.		No connection			
16	OUTD	0	When IC is standby mode, this terminal is set to "Hi-Z" to prevent loss of inefficient current through the output voltage setting resistor. Set CTL terminal to "H" level to output "L" level.			
17	-INC1	I	Current detection amplifier (Current Amp1) inverted input terminal			
18	N.C.		No connection			
19	+INC1	I	Current detection amplifier (Current Amp1) non-inverted input terminal			
20	CTL	I	Power supply control terminal Setting the CTL terminal at "L" level places the IC in the standby mode.			
21	FB123	0	Error amplifier (Error Amp1, 2, 3) output terminal			
22	–INE3	I	Error amplifier (Error Amp3) inverted input terminal			
23	RT		Triangular wave oscillation frequency setting resistor connection terminal			
24	XACOK	0	AC adapter voltage detection block ( AC Comp.) output terminal XACOK = Hi-Z when ACIN = H, XACOK = L when ACIN = L, XACOK = Hi-Z when CTL = L			
25	VH	0	Power supply terminal for FET drive circuit (VH = VCC - 6 V)			
26	OUT	0	External FET gate drive terminal			
27	VCC		Power supply terminal for reference voltage, control circuit, and output circuit			
28	CS		Soft-start setting capacitor connection terminal			

• MB39A126 : SSOP-24

Pin No.	Pin Name	I/O	Description			
1	-INC2	I	Current detection amplifier (Current Amp2) inverted input terminal			
2	OUTC2	0	Current detection amplifier (Current Amp2) output terminal			
3	+INE2	I	Error amplifier (Error Amp2) non-inverted input terminal			
4	-INE2	I	Error amplifier (Error Amp2) inverted input terminal			
5	ACOK	0	AC adapter voltage detection block (AC Comp.) output terminal ACOK = L when ACIN = H, ACOK = Hi-Z when ACIN = L, ACOK = Hi-Z when CTL = L			
6	VREF	0	Reference voltage output terminal			
7	ACIN	I	AC adapter voltage detection block (AC Comp.) input terminal			
8	-INE1	I	Error amplifier (Error Amp1) inverted input terminal			
9	+INE1	I	Error amplifier (Error Amp1) non-inverted input terminal			
10	OUTC1	0	Current detection amplifier (Current Amp1) output terminal			
11	SEL	I	Charge voltage setting switch terminal (3cells or 4cells) SEL terminal "H" level : Charge voltage setting 16.8 V (4cells) SEL terminal "L" level : Charge voltage setting 12.6 V (3cells)			
12	-INC1	I	Current detection amplifier (Current Amp1) inverted input terminal			
13	+INC1	I	Current detection amplifier (Current Amp1) non-inverted input terminal			
14	CTL	I	Power supply control terminal Setting the CTL terminal at "L" level places the IC in the standby mode.			
15	FB123	0	Error amplifier (Error Amp1, 2, 3) output terminal			
16	–INE3	I	Error amplifier (Error Amp3) inverted input terminal			
17	RT	—	Triangular wave oscillation frequency setting resistor connection terminal			
18	XACOK	0	AC adapter voltage detection block ( AC Comp.) output terminal XACOK = Hi-Z when ACIN = H, XACOK = L when ACIN = L, XACOK = Hi-Z when CTL = L			
19	VH	0	Power supply terminal for FET drive circuit (VH = VCC - 6 V)			
20	OUT	0	External FET gate drive terminal			
21	VCC	_	Power supply terminal for reference voltage, control circuit, and output circuit			
22	CS		Soft-start setting capacitor connection terminal			
23	GND	_	Ground terminal			
24	+INC2	I	Current detection amplifier (Current Amp2) non-inverted input terminal			

#### • MB39A126 : QFN-28

Pin No.	Pin Name	I/O	Description			
1	N.C.		No connection			
2	GND		Ground terminal			
3	+INC2	I	Current detection amplifier (Current Amp2) non-inverted input terminal			
4	N.C.		No connection			
5	-INC2	I	Current detection amplifier (Current Amp2) inverted input terminal			
6	OUTC2	0	Current detection amplifier (Current Amp2) output terminal			
7	+INE2	I	Error amplifier (Error Amp2) non-inverted input terminal			
8	–INE2	I	Error amplifier (Error Amp2) inverted input terminal			
9	ACOK	Ο	AC adapter voltage detection block (AC Comp.) output terminal ACOK = L when ACIN = H, ACOK = Hi-Z when ACIN = L, ACOK = Hi-Z when CTL = L			
10	VREF	0	Reference voltage output terminal			
11	ACIN	I	AC adapter voltage detection block (AC Comp.) input terminal			
12	–INE1	I	Error amplifier (Error Amp1) inverted input terminal			
13	+INE1	I	Error amplifier (Error Amp1) non-inverted input terminal			
14	OUTC1	0	Current detection amplifier (Current Amp1) output terminal			
15	N.C.		No connection			
16	SEL	I	Charge voltage setting switch terminal (3cells or 4cells) . SEL terminal "H" level : Charge voltage setting 16.8 V (4cells) SEL terminal "L" level : Charge voltage setting 12.6 V (3cells)			
17	-INC1	I	Current detection amplifier (Current Amp1) inverted input terminal			
18	N.C.		No connection			
19	+INC1	I	Current detection amplifier (Current Amp1) non-inverted input terminal			
20	CTL	I	Power supply control terminal Setting the CTL terminal at "L" level places the IC in the standby mode.			
21	FB123	0	Error amplifier (Error Amp1, 2, 3) output terminal			
22	-INE3	I	Error amplifier (Error Amp3) inverted input terminal			
23	RT		Triangular wave oscillation frequency setting resistor connection terminal			
24	XACOK	0	AC adapter voltage detection block ( AC Comp.) output terminal XACOK = Hi-Z when ACIN = H, XACOK = L when ACIN = L, XACOK = Hi-Z when CTL = L			
25	VH	0	Power supply terminal for FET drive circuit (VH = VCC - 6 V)			
26	OUT	0	External FET gate drive terminal			
27	VCC		Power supply terminal for reference voltage, control circuit, and output circuit			
28	CS		Soft-start setting capacitor connection terminal			

■ BLOCK DIAGRAMS





• MB39A126



### ■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Condition	Rat	ing	Unit
Farameter	Symbol	Condition	Min	Max	Unit
Power supply voltage	Vcc	VCC terminal		28	V
Output current	Ιουτ			60	mA
Peak output current	Ιουτ	$Duty \le 5\%$ (t = 1 / fosc × Duty)		700	mA
Dower dissipation	Po	Ta ≤ +25 °C (SSOP-24)	_	740* <sup>1</sup>	mW
Power dissipation	ΓD	Ta ≤ +25 °C (QFN-28)		3700* <sup>2</sup>	mW
Storage temperature	Tstg	—	-55	+125	°C

\*1 : When mounted on a 10cm square epoxy double-sided.

\*2 : The packages are mounted on the dual-sided epoxy board (10 cm × 10 cm) . Connect IC's radiation board at bottom side to potential of GND.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

### RECOMMENDED OPERATION CONDITIONS

Denementar	Querra ha a l	O an diti an		Value		11
Parameter	Symbol	Condition	MIN	TYP	MAX	Unit
Power supply voltage	Vcc	VCC terminal	8		25	V
Reference voltage Output current	IREF	—	-1		0	mA
VH terminal output current	І∨н	—	0		30	mA
	VINE	+INE, -INE terminal	0		5	V
Input voltage	VINC	+INC, -INC terminal	0		Vcc	V
CTL terminal input voltage	Vctl	—	0		25	V
Output current	Ιουτ	—	-45		+45	mA
Peak output current	Ιουτ	$\begin{array}{l} Duty \leq 5\% \\ (t = 1 \ / \ fosc \times Duty) \end{array}$	-600		+600	mA
ACIN terminal input Voltage	VACIN	—	0		Vcc	V
ACOK terminal output voltage	Vасок	—	0		25	V
ACOK terminal output current	Іасок	—	0		1	mA
XACOK terminal output voltage	Vхасок	—	0		25	V
XACOK terminal output current	Іхасок	—	0		1	mA
OUTD terminal output voltage : MB39A125	Voutd	—	0		17	V
OUTD terminal output current : MB39A125	Ιουτσ	_	0		2	mA
SEL terminal input voltage : MB39A126	Vsel	_	0		25	V
Oscillation frequency	fosc		100	300	500	kHz
Timing resistor	R⊤	—	27	47	130	kΩ
Soft-start capacitor	Cs			0.22	1.0	μF
VH terminal capacitor	Сун	—		0.1	1.0	μF
Reference voltage output capacitor	Cref	—		0.22	1.0	μF
Operating ambient Temperature	Та	—	-30	+25	+85	°C

Note : The terminal number which has been described in the text is the one of the SSOP-24P package after this.

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their representatives beforehand.

### ■ ELECTRICAL CHARACTERISTICS

(VCC = 19 V, VREF = 0 mA, Ta = +25  $^{\circ}$ C)

		Sym-	Pin		Value				
Para	Parameter		No.	Condition	Min	Тур	Max	Unit	Remarks
		V <sub>REF1</sub>	6	Ta = +25 °C	4.963	5.000	5.037	V	MB39A125
	Output	V <sub>REF2</sub>	6	Ta = −10 °C to +85 °C	4.95	5.000	5.05	V	MB39A125
1.	Output voltage	V <sub>REF1</sub>	6	Ta = +25 °C	4.943	4.980	5.017	V	MB39A126
Reference		VREF2	6	Ta = $-10 \degree$ C to $+85 \degree$ C	4.930	4.980	5.030	V	MB39A126
voltage block [REF]	Input stability	Line	6	VCC = 8 V to 25 V	_	3	10	mV	
	Load stability	Load	6	VREF = 0 mA to -1 mA	_	1	10	mV	
	Output current at short circuit	los	6	VREF = 1 V	-50	-25	-12	mA	
2.	Threshold	Vtlh	6	VREF = _	2.6	2.8	3.0	V	
Under voltage lockout	voltage	VTHL	6	VREF = T	2.4	2.6	2.8	V	
protection circuit block [UVLO]	Hysteresis width	Vн	6			0.2*		V	
3. Soft start block [SOFT]	Charge current	lcs	22		-14	-10	-6	μA	
4. Triangular	Oscillation frequency	fosc	20	RT = 47 kΩ	270	300	330	kHz	
wave oscillator block [OSC]	Frequency temperature stability	∆f/fdt	20	Ta = $-30 \degree C$ to $+85 \degree C$		1*		%	
	Input offset voltage	Vio	3, 4, 8, 9	FB123 = 2 V	_	1	5	mV	
	Input bias current	Ів	3, 4, 8, 9	_	-100	-30	_	nA	
5-1.	Common mode input voltage range	Vсм	3, 4, 8, 9	_	0		5	V	
Error amplifier	Voltage gain	Av	15	DC		100*		dB	
block [Error Amp1, Error Amp2]	Frequency bandwidth	BW	15	AV = 0 dB	_	1.3*	_	MHz	
		Vfbh	15		4.8	5.0		V	
	Output voltage	Vfbl	15	—		0.8	0.9	V	
	Output source current	ISOURCE	15	FB123 = 2 V		-120	-60	μA	
	Output sink current	Isink	15	FB123 = 2 V	2.0	4.0		mA	

\*: Standard design value

(VCC = 19 V, VREF = 0 mA, Ta = +25  $^{\circ}$ C)

Dam		Sym-	Pin	Oomalition		Value		11	Demerica
Para	ameter	bol	No.	Condition	Min	Тур	Max	Unit	Remarks
	Input current	line	16	-INE3 = 0 V	-100	-30	—	nA	MB39A125
	Voltage gain	Av	15	DC		100*	_	dB	
	Frequency bandwidth	BW	15	AV = 0 dB		1.3*		MHz	
	Output	Vfbh	15		4.8	5.0		V	
	voltage	Vfbl	15	—		0.8	0.9	V	
	Output source current	Isource	15	FB123 = 2 V	_	-120	-60	μA	
	Output sink current	Isink	15	FB123 = 2 V	2.0	4.0	_	mA	
		Vth1	16	FB123 = 2 V, Ta = +25 °C	4.179	4.200	4.220	V	MB39A125
5-2.		V <sub>TH2</sub>	16	FB123 = 2 V, Ta = -10 °C to +85 °C	4.169	4.200	4.231	V	MB39A125
Error amplifier block	Threshold	Vтнз	12	SEL = 5 V, FB123 = 2 V, Ta = +25 °C	16.700	16.800	16.900	V	MB39A126
[Error Amp3]	voltage	V <sub>TH4</sub>	12	SEL = 5 V, FB123 = 2 V, Ta = -10 °C to +85 °C	16.666	16.800	16.934	V	MB39A126
		Vth5	12	SEL = 0 V, FB123 = 2 V, Ta = +25 °C	12.525	12.600	12.675	V	MB39A126
		Vth6	12	SEL = 0 V, FB123 = 2 V, Ta = -10 °C to +85 °C	12.500	12.600	12.700	V	MB39A126
	OUTD terminal output leak current	Ileak	11	OUTD = 17 V		0	1	μA	MB39A125
	OUTD terminal output ON resistance	Ron	11	OUTD = 1 mA		35	50	Ω	MB39A125
	Input current	lin	12	-INC1 = 16.8 V		84	150	μA	MB39A126
	Input	R1	12, 16		105	150	195	kΩ	MB39A126
	resistance	R2	16		35	50	65	kΩ	MB39A126

\*: Standard design value

(VCC = 19 V, VREF = 0 mA, Ta = +25 °C)

Deren	nator	Sym-	Pin No.	Condition		Value		l lmit	it Remarks		
Paran	neter	bol		Condition	Min	Тур	Max	Unit	Remarks		
5-2.	SEL input	Von	11	Error Amp3 reference voltage = 4.2 V (4-cell setting)	2		25	V	MB39A126		
Error amplifier block [Error Amp3]	voltage	Voff	11	Error Amp3 reference voltage = 3.15 V (3-cell setting)	0		0.8	V	MB39A126		
	Input	SELH	11	SEL = 5 V		50	100	μA	MB39A126		
	current	ISELL	11	SEL = 0 V		0	1	μΑ	MB39A126		
	Input offset voltage	Vio	1, 12, 13, 24	+INC1 = +INC2 = -INC1 = -INC2 = 3 V to VCC	-3		+3	mV			
		I+INCH	13, 24	+INC1 = +INC2 = 3 V to VCC, $\Delta V_{IN} = -100 \text{ mV}$		20	30	μA			
		lanut	loout	I-inch	1, 12	+INC1 = +INC2 = 3 V to VCC, $\Delta V_{IN} = -100 \text{ mV}$		0.1	0.2	μA	MB39A125
	Input current	_	1	+INC1 = +INC2 = 3 V to VCC, $\Delta V_{IN} = -100 \text{ mV}$	_	0.1	0.2	μA	MB39A126		
6. Current		I+INCL	13, 24	+INC1 = +INC2 = 0 V, $\Delta V_{IN} = -100 mV$	-180	-120		μΑ			
Detection Amplifier		I-INCL	1, 12	+INC1 = +INC2 = 0 V, $\Delta V_{IN} = -100 mV$	-195	-130		μΑ			
Block [Current Amp1,		Voutc1	2, 10	+INC1 = +INC2 = 3 V to VCC, $\Delta V_{IN} = -100 \text{ mV}$	1.9	2.0	2.1	V			
Current Amp2]	Current detection	Voutc2	2, 10	+INC1 = +INC2 = 3 V to VCC, $\Delta V_{IN} = -20 \text{ mV}$	0.34	0.40	0.46	V			
	voltage	Vоитсз	2, 10	+INC1 = +INC2 = 0 V, $\Delta V_{IN} = -100 mV$	1.8	2.0	2.2	V			
		Voutc4	2, 10	+INC1 = +INC2 = 0 V, $\Delta V_{IN} = -20 mV$	0.2	0.4	0.6	V			
	Common mode input voltage range	Vсм	1, 12, 13, 24	_	0		Vcc	V			
	Voltage gain	Av	2, 10	+INC1 = +INC2 = 3 V to VCC, $\Delta V_{IN} = -100 \text{ mV}$	19	20	21	V/V	(Continued		

(VCC = 19 V, VREF = 0 mA, Ta = +25  $^{\circ}$ C)

Demon		Sym-	Din Ma	Condition	·	Value		11	Re-
Paran	Parameter		Pin No.	Condition	Min	Тур	Max	Unit	marks
6.	Frequency bandwidth	BW	2, 10	AV = 0 dB		2*		MHz	
Current Detection	Output	Vоитсн	2, 10	—	4.7	4.9		V	
Amplifier	voltage	VOUTCL	2, 10	—		20	200	mV	
Block [Current Amp1, Current	Output source cur- rent	ISOURCE	2, 10	OUTC1 = OUTC2 = 2 V		-2	-1	mA	
Amp2]	Output sink current	Isink	2, 10	OUTC1 = OUTC2 = 2 V	150	300	—	μΑ	
7.		Vtl	15	Duty cycle = 0%	1.4	1.5		V	
PWMComp. Block [PWM Comp.]	Threshold voltage	Vтн	15	Duty cycle = 100%		2.5	2.6	V	
	Output source cur- rent	ISOURCE	20	$\begin{array}{l} OUT = 13 \text{ V},\\ Duty \leq 5\%\\ (t = 1 \ / \ \text{fosc} \times \text{Duty}) \end{array}$		-400*		mA	
8. Output block	Output sink current	Isink	20	$\begin{array}{l} OUT = 19 \text{ V},\\ Duty \leq 5\%\\ (t = 1 \ / \ \text{fosc} \times \text{Duty}) \end{array}$		400*		mA	
[OUT]	Output ON	Rон	20	OUT = -45 mA		6.5	9.8	Ω	
	resistance	Rol	20	OUT = 45 mA		5.0	7.5	Ω	
	Rise time	tr1	20	OUT = 3300 pF		50*		ns	
	Fall time	tf1	20	OUT = 3300 pF		50*		ns	
9. Low Input	Threshold	Vtlh	21	VCC = _, −INC1 = 16.8 V	17.2	17.4	17.6	V	
Voltage Detection	voltage	Vthl	21	VCC = ་⊻ , −INC1 = 16.8 V	16.8	17.0	17.2	V	
Block [UV Comp.]	Hysteresis width	Vн	21	_		0.4*		V	
10.	Threshold	Vtlh	7		1.3	1.4	1.5	V	
AC Adapter Voltage	voltage	Vthl	7	ACIN = Ţ	1.2	1.3	1.4	V	
Detection Block [AC Comp.]	Hysteresis width	Vн	7	_		0.1*		V	

\*: Standard design value

(Continued)

(VCC = 19 V, VREF = 0 mA, Ta = +25  $^{\circ}$ C)

Doro	motor	Sym-	Pin	Condition		Value		Unit	Re-
Para	meter	bol No.		Condition	Min	Тур	Max	Unit	marks
	ACOK terminal output leak current	Ileak	5	ACOK = 25 V		0	1	μΑ	
10. AC Adapter Voltage	ACOK terminal output ON resistance	Ron	5	ACOK = 1 mA		200	400	Ω	
Detection XACOK Block termina [AC Comp.] output I current XACOK termina output 0	XACOK terminal output leak current	Ileak	18	XACOK = 25 V	_	0	1	μΑ	
	XACOK terminal output ON resistance	Ron	18	XACOK = 1 mA	_	200	400	Ω	
11.	CTL input	Von	14	IC operation mode	2	_	25	V	
Power Supply	voltage	Voff	14	IC standby mode	0		0.8	V	
Control Block		Істін	14	CTL = 5 V		100	150	μΑ	
[CTL]	Input current	ICTLL	14	CTL = 0 V		0	1	μA	
12. Bias Voltage Block [VH]	Output Voltage	Vн	19	VCC = 8 V to 25 V, VH = 0 mA to 30 mA	Vcc – 6.5	Vcc – 6.0	Vcc – 5.5	V	
13.	Standby current	Iccs	21	CTL = 0 V	_	0	10	μA	
General	Power supply current	lcc	21	CTL = 5 V		5	7.5	mA	

\*: Standard design value

### ■ TYPICAL CHARACTERISTICS











### FUNCTIONAL DESCRIPTION

#### 1. DC/DC Converter Block

#### (1) Reference voltage block (REF)

The reference voltage circuit uses the voltage supplied from the VCC terminal (pin 21) to generate a temperature compensated, stable voltage (5.0 V Typ) used as the reference power supply voltage for the IC's internal circuitry.

This block can also be used to obtain a load current to a maximum of 1 mA from the reference voltage VREF terminal (pin 6) .

#### (2) Triangular wave oscillator block (OSC)

The triangular wave oscillator block has built-in capacitor for frequency setting into and generates the triangular wave oscillation waveform by connecting the frequency setting resistor with the RT terminal (pin 17).

The triangular wave is input to the PWM comparator circuits on the IC.

#### (3) Error amplifier block (Error Amp1)

This amplifier detects the output signal from the current detection amplifier (Current Amp1), compares this to the +INE1 terminal (pin 9), and outputs a PWM control signal to be used in controlling the charge current.

In addition, an arbitrary loop gain can be set up by connecting a feedback resistor and capacitor between the FB123 terminal (pin 15) and –INE1 terminal (pin 8), providing stable phase compensation to the system.

#### (4) Error amplifier block (Error Amp2)

This amplifier detects the output signal from the current detection amplifier (Current Amp2), compares this to the +INE2 terminal (pin 3), and outputs a PWM control signal to be used in controlling the charge current.

In addition, an arbitrary loop gain can be set up by connecting a feedback resistor and capacitor between the FB123 terminal (pin 15) and –INE2 terminal (pin 4), providing stable phase compensation to the system.

#### (5) Error amplifier block (Error Amp3)

This error amplifier (Error Amp3) detects the output voltage from the DC/DC converter and outputs the PWM control signal. MB39A125 can set the desired level of output voltage from 1 cell to 4 cells by connecting external output voltage setting resistors to the error amplifier inverted input terminal. MB39A126 can set the output voltage for 3 cells or 4 cells by SEL terminal (pin 11) input.

In addition, an arbitrary loop gain can be set by connecting a feedback resistor and capacitor from the FB123 terminal (pin 15) to the –INE3 terminal (pin 16), enabling stable phase compensation to the system.

#### (6) Current detection amplifier block (Current Amp1)

The current detection amplifier (Current Amp1) detects a voltage drop which occurs between both ends of the output sense resistor (RS2) due to the flow of the charge current, using the +INC1 terminal (pin 13) and -INC1 terminal (pin 12). The signal amplified to 20 times is output to the OUTC1 terminal (pin 10).

#### (7) Current detection amplifier block (Current Amp2)

The current detection amplifier (Current Amp2) detects a voltage drop which occurs between both ends of the output sense resistor (RS1) due to the flow of the AC adapter current, using the +INC2 terminal (pin 24) and -INC2 terminal (pin 1). The signal amplified to 20 times is output to the OUTC2 terminal (pin 2).

#### (8) PWM comparator block (PWM Comp.)

The PWM comparator circuit is a voltage-pulse width converter for controlling the output duty of the error amplifiers (Error Amp1 to Error Amp3) depending on their output voltage.

The PWM comparator circuit compares the triangular wave voltage the lowest generated by the triangular wave oscillator to the error amplifier output voltage and turns on the external output transistor, during the interval in which the triangular wave voltage is lower than the error amplifier output voltage.

#### (9) Output block (OUT)

The output circuit uses a totem-pole configuration capable of driving an external Pch MOS FET.

The output "L" level sets the output amplitude to 6 V (Typ) using the voltage generated by the bias voltage block (VH) .

This results in increasing conversion efficiency and suppressing the withstand voltage of the connected external transistor in a wide range of input voltages.

#### (10) Power supply control block (CTL)

Setting the CTL terminal (pin 14) low places the IC in the standby mode. (The power supply current is  $10\mu A$  at maximum in the standby mode.)

CTL	Power	OUTD
L	OFF (Standby)	Hi-Z
Н	ON (Active)	L

#### CTL function table : MB39A125

#### CTL function table : MB39A126

CTL	Power
L	OFF (Standby)
Н	ON (Active)

#### (11) Bias voltage block (VH)

The bias voltage circuit outputs  $V_{CC}$  – 6 V (Typ) as the minimum potential of the output circuit. In the standby mode, this circuit outputs the potential equal to  $V_{CC}$ .

#### 2. Protection Functions

#### (1) Under voltage lockout protection circuit block (UVLO)

The transient state or a momentary decrease in power supply voltage or internal reference voltage (VREF), which occurs when the power supply (VCC) is turned on, may cause malfunctions in the control IC, resulting in breakdown or deterioration of the system.

To prevent such malfunction, the under voltage lockout protection circuit detects internal reference voltage drop and fixes the OUT terminal (pin 20) to the "H" level. The system restores voltage supply when the internal reference voltage reaches the threshold voltage of the under voltage lockout protection circuit.

#### Protection circuit (UVLO) operation function table : MB39A125

When UVLO is operating (VREF voltage is lower than UVLO threshold voltage, the logic of the following terminal is fixed.)

OUTD	OUT	CS	ACOK	XACOK
Hi-Z	Н	L	Н	L

#### Protection circuit (UVLO) operation function table : MB39A126

When UVLO is operating (VREF voltage is lower than UVLO threshold voltage, the logic of the following terminal is fixed.)

OUT	CS	ACOK	XACOK
Н	L	Н	L

#### (2) Low input voltage detection block (UV Comp.)

UV Comp. detects that power supply voltage (VCC) is lower than the battery voltage +0.2 V (Typ) and fixes the OUT terminal (pin 20) to the "H" level.

The system restores voltage supply when the power supply voltage reaches the threshold voltage of the AC adapter detection block.

#### Protection circuit (UV Comp.) operation function table : MB39A125

When UV Comp. is operating (VCC voltage is lower than UV Comp. threshold voltage, the logic of the following terminal is fixed.)

OUTD	OUT	CS
L	Н	L

#### Protection circuit (UV Comp.) operation function table : MB39A126

When UV Comp. is operating (VCC voltage is lower than UV Comp. threshold voltage, the logic of the following terminal is fixed.)

OUT	CS
Н	L

#### 3. Detection Function

#### (1) AC adapter voltage detection block (AC Comp.)

When ACIN terminal (pin 7) voltage is lower than 1.3 V (Typ), AC adapter voltage detection block (AC Comp.) outputs "Hi-Z" level to the ACOK terminal (pin 5) and outputs "L" level to the XACOK terminal (pin 18). When CTL terminal (pin 14) is set to "L" level, ACOK terminal (pin 5) and XACOK terminal (pin 18) are fixed to "Hi-Z" level.

ACIN	ACOK	ХАСОК
Н	L	Hi-Z
L	Hi-Z	L

#### 4. Switch Function : MB39A126

The charge voltage can be set to 16.8 V/12.6 V with the SEL terminal (pin 11).

#### **SEL** function table

SEL	DC/DC output setting voltage
Н	16.8 V
L	12.6 V

### ■ CONSTANT CHARGING VOLTAGE AND CURRENT OPERATION

MB39A125/126 is DC/DC converter with the pulse width modulation (PWM) .

MB39A125 is in the output voltage control loop, the Error Amp3 compares internal voltage reference voltage 4.2 V and DC/DC converter output to output the PWM controlled signal.

MB39A126 is in the output voltage control loop, the Error Amp3 compares internal voltage reference voltage 4.2 V/3.15 V and DC/DC converter output to output the PWM controlled signal.

In the charging current control loop, the voltage drop generated at both ends of charging current sense resistor (RS2) is sensed by +INC1 terminal (pin 13), -INC1 terminal (pin 12) of Current Amp1, and the signal is output to OUTC1 terminal (pin 10), which is amplified by 20 times. Error Amp1 compares the OUTC1 terminal (pin 10) voltage, which is the output of Current Amp1, and +INE1 terminal (pin 9) to output the PWM control signal and regulates the charging current.

In the AC adapter current control loop, the voltage drop generated at both ends of AC adapter current sense resistor (RS1) is sensed by +INC2 terminal (pin 24), -INC2 terminal (pin 1) of Current Amp2, and the signal is output to OUTC2 terminal (pin 2), which is amplified by 20 times. Error Amp2 compares OUTC2 terminal (pin 2) voltage, which is output of Current Amp2, and +INE2 terminal (pin 3) voltage and outputs PWM controlled signal, and it limits the charging current due to the AC adapter current not to exceed the setting value.

The PWM comparator compares the triangular wave to the smallest terminal voltage among the Error AMP1, Error AMP2 and Error AMP3. And the triangular wave voltage generated by the triangular wave oscillator. When the triangular wave voltage is smaller than the error amplifier output voltage, the main side output transistor is turned on.

### SETTING THE CHARGE VOLTAGE

#### MB39A125

The charging voltage (DC/DC output voltage) can be set by connecting external output voltage setting resistors (R3, R4) to the –INE3 terminal (pin 16). Be sure to select a resistor value that allows you to ignore the on-resistance (35  $\Omega$ , 1 mA) of the internal FET connected to the OUTD terminal (pin 11).

Battery charging voltage : Vo

Vo (V) = (R3 + R4) / R4  $\times$  4.2 (V)



#### MB39A126

The setting of the charge voltage is switched to 3cells or 4cells by the SEL terminal (pin 11).

Charge voltage is set to 16.8 V when SEL terminal is "H" level, and charge voltage is set to 12.6 V when SEL terminal is "L" level.

Battery charging voltage : Vo



### ■ SETTING THE CHARGE CURRENT

The charge current value can be set at the analog voltage value of the +INE1 terminal (pin 9).

Charge current formula : Ichg (A) =  $V_{+INE1}$  (V) / (20 × R<sub>S1</sub> ( $\Omega$ )) Charge current setting voltage :  $V_{+INE1}$  (V) = 20 × Ichg (A) × R<sub>S1</sub> ( $\Omega$ )

### SETTING THE INPUT CURRENT

The input limit current value can be set at the analog voltage value of the +INE2 terminal (pin 3) .

Input current formula :  $I_{IN}$  (A) = V<sub>+INE2</sub> (V) / (20 × R<sub>S2</sub> ( $\Omega$ ) ) Input current setting voltage : V<sub>+INE2</sub> (V) = 20 × I<sub>IN</sub> (A) × R<sub>S2</sub> ( $\Omega$ )

### ■ SETTING THE TRIANGULAR WAVE OSCILLATION FREQUENCY

The triangular wave oscillation frequency can be set by the timing resistor ( $R_T$ ) connected to the RT terminal (pin 17).

Triangular wave oscillation frequency fosc fosc (kHz)  $\Rightarrow$  14100 / R<sub>T</sub> (k $\Omega$ )

### SETTING THE SOFT-START TIME

Soft-start function prevents rush current at start-up of IC when the Soft-start capacitor (Cs) is connected to the CS terminal (pin 22). This IC charges external soft-start capacitor (Cs) with 10  $\mu$ A after CTL terminal (pin 14) voltage level becomes high and IC starts (when Vcc  $\geq$  UVLO threshold voltage).

Output ON duty depends on PWM comparator, which compares the FB123 terminal (pin 15) voltage with the triangular wave oscillator output voltage.

During soft start, FB123 terminal (pin 15) voltage increases with sum voltage of CS terminal and diode voltage. Therefore, the output voltage of the DC/DC converter and current increase can be set by output ON duty in proportion to rise of CS terminal (pin 22) voltage. The ON Duty is affected by the ramp voltage of FB123 terminal (pin 15) until an output voltage of one Error Amp reaches the DC/DC converter loop controlled voltage.

Soft-start time is obtained from the following formula :

Soft-start time : ts (time to output on duty 80 %)

ts (s)  $\Rightarrow$  0.13 × Cs ( $\mu$ F)



### ■ TRANSIENT RESPONSE AT LOAD-STEP

The constant voltage control loop and the constant current control loop are independent. With the load-step, these two control loops change.

The battery voltage and current overshoot are generated by the delay time of the control loop when the mode changes. The delay time is determined by phase compensation constant. When the battery is removed if the charge control is switched from the constant current control to the constant voltage control, and the charging voltage does overshoot by generating the period controlled with high duty by output setting voltage. The excessive voltage is not applied to the battery because the battery is not connected.

When the battery is connected if the charge control is switched from the constant voltage control to the constant current control, and the charging current does overshoot by generating the period controlled with high duty by charge current setting.

The battery pack manufacturer in Japan thinks it is not the problem the current overshoot of 10 ms or less.



### ■ AC ADAPTER DETECTION FUNCTION

When ACIN terminal (pin 7) voltage is lower than 1.3 V (Typ), AC adapter voltage detection block (AC Comp.) outputs "Hi-Z" level to the ACOK terminal (pin 5) and outputs "L" level to the XACOK terminal (pin 18). When CTL terminal (pin 14) is set to "L" level, ACOK terminal (pin 5) and XACOK terminal (pin 18) are fixed to "Hi-Z" level.

#### (1) AC adapter presence

If you connect as shown in the figure below the presence of AC adapter can be easily detected because the signal is output from the ACOK terminal (pin 5) to microcomputer etc. In this case, if the CTL terminal is set to "L" level, IC becomes the standby state ( $I_{CC} = 0 \ \mu A \ Typ$ ).



#### (2) Automatic changing system power supply between AC adapter and battery

The AC adapter voltage is detected and external switch at input side and battery side can be changed automatically with the connection as follows. Connect CTL terminal (pin 14) to VCC terminal (pin 21) for this function. OFF duty cycle becomes 100% when CS terminal (pin 22) voltage is made to be 0 V, if it is needed after full charge.



#### (3) Battery selector function

When control signal from microcomputer etc. is input to ACIN terminal (pin 7) as shown in the following diagram, ACOK terminal (pin 5) output voltage and XACOK terminal (pin 18) output voltage are controlled to select one of the two batteries for charge. Connect CTL terminal (pin 14) to VCC terminal (pin 21) for this function. OFF duty cycle becomes 100% when CS terminal (pin 22) voltage is made to be 0 V, if it is needed after full charge.


### (4) When AC Comp. is not used

When AC Comp. (ACIN (pin 7), ACOK (pin 5), and XACOK (pin 18) terminals) is not used as follows, connect the ACIN (pin 7), ACOK (pin 5), and XACOK (pin 18) terminals to GND terminal (pin 23).

And connect VCC terminal (pin 21) to system, as follows, to avoid the reverse current from the battery to the VCC terminal (pin 21).



## ■ PHASE COMPENSATION









Notes : 1) Please review the Error Amp frequency characteristics, when LC filter parameter is modified.

2) When the ceramic capacitor is used as smoothing capacitor Co, phase margin is reduced because ESR of the ceramic capacitor is extremely small as shown in "Frequency Characteristics of LC filter which is using low ESR".

Therefore, change phase compensation of Error Amp or create resistance equivalent to ESR using pattern.



## ■ PROCESSING WITHOUT USING OF THE CURRENT AMP1 AND AMP2

When Current Amp is not used, connect the +INC1 terminal (pin 13) , +INC2 terminal (pin 24) , -INC1 terminal (pin 12) , and -INC2 terminal (pin 1) to VREF terminal (pin 6) , and then leave OUTC1 terminal (pin 10) and OUTC2 terminal (pin 2) open.



## ■ PROCESSING WITHOUT USING OF THE ERROR AMP1 AND AMP2

When Error Amp is not used, leave FB123 terminal (pin 15) open, connect the –INE1 terminal (pin 8) and –INE2 terminal (pin 4) to GND, and connect +INE1 terminal (pin 9) and +INE2 terminal (pin 3) to VREF terminal (pin 6).



## ■ PROCESSING WITHOUT USING OF THE CS TERMINAL

When soft-start function is not used, leave the CS terminal (pin 22) open.

Connection when no soft-start time is specified





(Continued)



### ■ APPLICATION EXAMPLE 1

• MB39A125



## ■ PARTS LIST 1

### • MB39A125

COMPONENT	ITEM	SPECI	FICATION	VENDOR	PARTS No.
Q1, Q2, Q3	Pch FET	VDS = -30 V, ID = -7.0 A		NEC	μPA2714GR
D1	Diode	VF = 0.42 V (Max) , At IF = 3 A		ROHM	RB053L-30
L1	Inductor	15 μH	$3.6 \text{ A}, 50 \text{ m}\Omega$	SUMIDA	CDRH104R-150
C1, C3, C4	Ceramics Condenser	10 μF	25 V	TDK	C3225X5R1E106K
C6	Ceramics Condenser	2200 pF	50 V	TDK	C1608JB1H222K
C7, C12	Ceramics Condenser	0.1 μF	50 V	TDK	C1608JB1H104K
C8, C10	Ceramics Condenser	6800 pF	50 V	TDK	C1608JB1H682K
C9, C11	Ceramics Condenser	0.22 μF	16 V	TDK	C1608JB1C224K
C13	Ceramics Condenser	22 pF	50 V	TDK	C1608CH1H220J
C14	Ceramics Condenser	47 pF	50 V	TDK	C1608CH1H470J
C15	Ceramics Condenser	0.22 μF	25 V	TDK	C2012JB1E224K
RS1	Resistor	15 mΩ	1%	KOA	SL1TTE15LOF
RS2	Resistor	$33 \text{ m}\Omega$	1%	KOA	SL1TTE33LOF
R3	Resistor	33 kΩ	0.5%	ssm	RR0816P-333-D
R4	Resistor	47 kΩ	0.5%	ssm	RR0816P-473-D
R5, R8	Resistor	100 kΩ	0.5%	ssm	RR0816P-104-D
R6, R7	Resistor	10 kΩ	0.5%	ssm	RR0816P-103-D
R9	Resistor	36 kΩ	0.5%	ssm	RR0816P-363-D
R10	Resistor	20 kΩ	0.5%	ssm	RR0816P-203-D
R11	Resistor	1.1 kΩ	0.5%	ssm	RR0816P-112-D
R12	Resistor	30 kΩ	0.5%	ssm	RR0816P-303-D
R13	Resistor	20 kΩ	0.5%	ssm	RR0816P-203-D
R14	Resistor	15 kΩ	0.5%	ssm	RR0816P-153-D
R15	Resistor	68 kΩ	0.5%	ssm	RR0816P-683-D
R16	Resistor	10 kΩ	0.5%	ssm	RR0816P-103-D
R17	Resistor	51 kΩ	0.5%	ssm	RR0816P-513-D
R18	Resistor	24 kΩ	0.5%	ssm	RR0816P-243-D
R19, R21, R23	Resistor	100 kΩ	0.5%	ssm	RR0816P-104-D
R20	Resistor	56 kΩ	0.5%	ssm	RR0816P-563-D
R22	Resistor	200 kΩ	0.5%	ssm	RR0816P-204-D

Note : NEC	: NEC Corporation
ROHM	: ROHM CO., LTD.
SUMIDA	: Sumida Corporation
TDK	: TDK Corporation
KOA	: KOA Corporation
ssm	: SUSUMU CO., LTD.

### ■ APPLICATION EXAMPLE 2

• MB39A126



## ■ PARTS LIST 2

### • MB39A126

COMPONENT	ITEM	SPECI	FICATION	VENDOR	PARTS No.
Q1, Q2, Q3	Pch FET	VDS = -30	V, ID = -7.0 A	NEC	μPA2714GR
D1	Diode	VF = 0.42 V (I	Max), At $IF = 3 A$	ROHM	RB053L-30
L1	Inductor	15 μH	$3.6 \text{ A}, 50 \text{ m}\Omega$	SUMIDA	CDRH104R-150
C1, C3, C4	Ceramics Condenser	10 μF	25 V	TDK	C3225X5R1E106K
C6	Ceramics Condenser	2200 pF	50 V	TDK	C1608JB1H222K
C7, C12	Ceramics Condenser	0.1 μF	50 V	TDK	C1608JB1H104K
C8, C10	Ceramics Condenser	6800 pF	50 V	TDK	C1608JB1H682K
C9, C11	Ceramics Condenser	0.22 μF	16 V	TDK	C1608JB1C224K
C13	Ceramics Condenser	22 pF	50 V	TDK	C1608CH1H220J
C14	Ceramics Condenser	47 pF	50 V	TDK	C1608CH1H470J
C15	Ceramics Condenser	0.22 μF	25 V	TDK	C2012JB1E224K
RS1	Resistor	15 mΩ	1%	KOA	SL1TTE15LOF
RS2	Resistor	$33 \text{ m}\Omega$	1%	KOA	SL1TTE33LOF
R3	Resistor	33 kΩ	0.5%	ssm	RR0816P-333-D
R4	Resistor	47 kΩ	0.5%	ssm	RR0816P-473-D
R5, R8	Resistor	100 kΩ	0.5%	ssm	RR0816P-104-D
R6, R7	Resistor	10 kΩ	0.5%	ssm	RR0816P-103-D
R9	Resistor	36 kΩ	0.5%	ssm	RR0816P-363-D
R10	Resistor	20 kΩ	0.5%	ssm	RR0816P-203-D
R11	Resistor	1.1 kΩ	0.5%	ssm	RR0816P-112-D
R12	Resistor	30 kΩ	0.5%	ssm	RR0816P-303-D
R13	Resistor	20 kΩ	0.5%	ssm	RR0816P-203-D
R14	Resistor	15 kΩ	0.5%	ssm	RR0816P-153-D
R15	Resistor	68 kΩ	0.5%	ssm	RR0816P-683-D
R16	Resistor	10 kΩ	0.5%	ssm	RR0816P-103-D
R17	Resistor	51 kΩ	0.5%	ssm	RR0816P-513-D
R18	Resistor	24 kΩ	0.5%	ssm	RR0816P-243-D
R19	Resistor	100 kΩ	0.5%	ssm	RR0816P-104-D
R20	Resistor	56 kΩ	0.5%	ssm	RR0816P-563-D

Note : NEC	: NEC Corporation
ROHM	: ROHM CO., LTD.
SUMIDA	: Sumida Corporation
TDK	: TDK Corporation
KOA	: KOA Corporation
ssm	: SUSUMU CO., LTD.

## SELECTION OF COMPONENTS

### Pch MOS FET

The Pch MOS FET for switching use should be rated for at least +20% more than the input voltage. To minimize continuity loss, use a FET with low R<sub>DS</sub> (ON) between the drain and source. For high input voltage and high frequency operation, on-cycle switching loss will be higher so that power dissipation must be considered. In this application, the NEC  $\mu$ PA2714GR is used. Continuity loss, on/off switching loss, and total loss are determined by the following formulas. The selection must ensure that peak drain current does not exceed rated values.

Continuity loss : Pc

 $Pc = Id^2 \times Rds (ON) \times Duty$ 

On-cycle switching loss : Ps (ON)

 $P_{S(ON)} = \frac{V_{D(Max)} \times I_{D} \times tr \times fosc}{6}$ 

Off-cycle switching loss : Ps (OFF)

 $\mathsf{P}_{\mathsf{S}(\mathsf{OFF})} = \frac{\mathsf{V}_{\mathsf{D}(\mathsf{Max})} \times \mathsf{I}_{\mathsf{D}(\mathsf{Max})} \times \mathsf{tf} \times \mathsf{fosc}}{6}$ 

Total loss : PT

 $P_T = P_C + P_{S(ON)} + P_{S(OFF)}$ 

Example) Using the  $\mu$ PA2714GR 16.8 V setting

Input voltage V<sub>IN (Max)</sub> = 25 V, output voltage V<sub>0</sub> = 16.8 V, drain current I<sub>D</sub> = 3 A, oscillation frequency fosc = 300 kHz, L = 15  $\mu$ H, drain-source on resistance R<sub>DS (ON)</sub> = 18 mΩ, tr = 15 ns, tf = 42 ns

Drain current (Max) : ID (Max)

$$I_{D (Max)} = I_{0} + \frac{V_{IN} - V_{0}}{2L} t_{0N}$$

$$= 3 + \frac{25 - 16.8}{2 \times 15 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.672$$

$$\Rightarrow 3.6 \text{ A}$$

Drain current (Min) : ID (Min)

$$I_{D (Min)} = I_{O} - \frac{V_{IN} - V_{O}}{2L} t_{ON}$$
$$= 3 - \frac{25 - 16.8}{2 \times 15 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.672$$
$$\Rightarrow 2.4 \text{ A}$$

 $P_{C} = I_{D^{2}} \times R_{DS(ON)} \times Duty$ 

- $= \ 3^2 \times 0.018 \times 0.672$
- ≑ <u>0.109 W</u>

 $V_{\text{D}} \times I_{\text{D}} \times tr \times \text{fosc}$ Ps (ON) = -----6  $25\times3\times15\times10^{-9}\times300\times10^{3}$ = -6 ≑ <u>0.056 W</u>  $V_{D} \times I_{D (Max)} \times tf \times fosc$  $P_{S(OFF)} = -$ 6  $25\times3.6\times42\times10^{_9}\times300\times10^{_3}$ = -6 ≑ <u>0.189 W</u>

 $P_T = P_C + P_{S(ON)} + P_{S(OFF)}$ 

The above power dissipation figures for the  $\mu$ PA2714GR are satisfied with ample margin at 2.0 W.

#### 12.6 V setting

Input voltage V<sub>IN (Max)</sub> = 22 V, output voltage V<sub>0</sub> = 12.6 V, drain current I<sub>D</sub> = 3 A, oscillation frequency fosc = 300 kHz, L = 15  $\mu$ H, drain-source on resistance R<sub>DS (ON)</sub> = 18 mΩ, tr = 15 ns, tf = 42 ns

Drain current (Max) : ID (Max)

$$I_{D (Max)} = I_{0} + \frac{V_{IN} - V_{0}}{2L} t_{ON}$$
$$= 3 + \frac{22 - 12.6}{2 \times 15 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.572$$
$$\Rightarrow 3.6 \text{ A}$$

Drain current (Min) : ID (Min)

$$I_{D (Min)} = I_{O} - \frac{V_{IN} - V_{O}}{2L} t_{ON}$$
$$= 3 - \frac{22 - 12.6}{2 \times 15 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.572$$
$$\Rightarrow 2.4 \text{ A}$$

#### $P_{C} = I_{D^2} \times R_{DS(ON)} \times Duty$

- $= 3^2 \times 0.018 \times 0.572$
- ≑ <u>0.093 W</u>

 $P_{S(ON)} = \frac{V_{D} \times I_{D} \times tr \times fosc}{6}$   $= \frac{22 \times 3 \times 15 \times 10^{-9} \times 300 \times 10^{3}}{6}$   $\Rightarrow 0.050 \text{ W}$   $P_{S(OFF)} = \frac{V_{D} \times I_{D(Max)} \times tf \times fosc}{6}$   $= \frac{22 \times 3.6 \times 42 \times 10^{-9} \times 300 \times 10^{3}}{6}$   $\Rightarrow 0.166 \text{ W}$ 

 $P_T = P_C + P_{S(ON)} + P_{S(OFF)}$ 

- $\Rightarrow 0.093 + 0.050 + 0.166$
- ≑ <u>0.309 W</u>

The above power dissipation figures for the µPA2714GR are satisfied with ample margin at 2.0 W.

The Pch MOS FET for switching use must use the one of more than input voltage +20%.

FET which operates when the AC adapter is connected should select FET which satisfies the current decided by sense resistance R1 enough. Because FET which operates when the AC adapter is not connected becomes a supply by the battery, it is necessary to select FET which satisfies the current of the system enough.

In this application, the NEC  $\mu$ PA2714GR is used.

#### Inductor

In selecting inductors, it is of course essential not to apply more current than the rated capacity of the inductor, but also to note that the lower limit for ripple current is a critical point that if reached will cause discontinuous operation and a considerable drop in efficiency. This can be prevented by choosing a higher inductance value, which will enable continuous operation under light-loads.

Note that if the inductance value is too high, however, direct current resistance (DCR) is increased and this will also reduce efficiency. The inductance must be set at the point where efficiency is greatest.

Note also that the DC superimposition characteristic becomes worse as the load current value approaches the rated current value of the inductor, so that the inductance value is reduced and ripple current increases, causing loss of efficiency.

The selection of rated current value and inductance value will vary depending on where the point of peak efficiency lies with respect to load current.

Inductance values are determined by the following formulas.

The L value for all load current conditions is set so that the peak to peak value of the ripple current is 1/2 the load current or less.

Inductance value : L

$$L \ge \frac{2(V_{IN} - V_0)}{I_0} t_{ON}$$

16.8 V output Example)  $L \geq \frac{2 (V_{IN (Max)} - Vo)}{Io} t_{ON}$  $\geq \frac{2 \times (25 - 16.8)}{3} \times \frac{1}{300 \times 10^{3}} \times 0.672$  $\geq 12.2 \,\mu\text{H}$ 12.6 V output Example)

$$L \geq \frac{2 (V_{IN (Max)} - Vo)}{Io} toN$$
$$\geq \frac{2 \times (22 - 12.6)}{3} \times \frac{1}{300 \times 10^3} \times 0.572$$
$$\geq 12.0 \,\mu\text{H}$$

Inductance values derived from the above formulas are values that provide sufficient margin for continuous operation at maximum load current, but at which continuous operation is not possible at light loads. It is therefore necessary to determine the load level at which continuous operation becomes possible. In this application, the SUMIDA CDRH104R-150 is used. The following formula is available to obtain the load current as a continuous current condition when 15  $\mu$ H is used.

The value of the load current satisfying the continuous current condition : lo

$$Io \geq \frac{Vo}{2L} toperators$$

Example) Using the CDRH104R-150

15  $\mu H$  (tolerance  $\pm$  30%) , rated current = 3.6 A 16.8 V output

$$lo \geq \frac{Vo}{2L} toFF$$
  
$$\geq \frac{16.8}{2 \times 15 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times (1 - 0.672)$$
  
$$\geq 0.61 A$$

12.6 V output

Io ≥ 
$$\frac{V_0}{2L}$$
 toFF  
≥  $\frac{12.6}{2 \times 15 \times 10^{-6}} \times \frac{1}{300 \times 10^3} \times (1 - 0.572)$   
≥  $0.60 \text{ A}$ 

To determine whether the current through the inductor is within rated values, it is necessary to determine the peak value of the ripple current as well as the peak-to-peak values of the ripple current that affects the output ripple voltage. The peak value and peak-to-peak value of the ripple current can be determined by the following formulas.

Peak Value : I∟

$$I_L \ge I_0 + \frac{V_{IN} - V_0}{2L} t_{ON}$$

Peak-to-peak Value : ΔIL

$$\Delta I_{L} = \frac{V_{IN} - V_{O}}{L} t_{ON}$$

Example) Using the CDRH104R-150 15  $\mu H$  (tolerance  $\pm$  30%) , rated current = 3.6 A

Peak Value

16.8 V output

$$I_{L} \geq I_{0} + \frac{V_{IN} - V_{0}}{2L} t_{0N}$$

$$\geq 3 + \frac{25 - 16.8}{2 \times 15 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.672$$

$$\geq 3.6 \text{ A}$$

12.6 V output

$$I_{L} \geq I_{0} + \frac{V_{IN} - V_{0}}{2L} t_{0N}$$
$$\geq 3 + \frac{22 - 12.6}{2 \times 15 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.572$$
$$\geq 3.6 \text{ A}$$

Peak-to-peak Value 16.8 V output

$$\Delta I_{L} = \frac{V_{IN} - V_{O}}{L} t_{ON}$$
$$= \frac{25 - 16.8}{15 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.672$$
$$\Rightarrow 1.22 \text{ A}$$

12.6 V output

$$\Delta I_{L} = \frac{V_{IN} - V_{O}}{L} t_{ON}$$
$$= \frac{22 - 12.6}{15 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.572$$
$$\Rightarrow 1.2 \text{ A}$$

### • Flyback diode

Shottky barrier diode (SBD) is generally used for the flyback diode when the reverse voltage to the diode is less than 40V. The SBD has the characteristics of higher speed in terms of faster reverse recovery time, and lower forward voltage, and is ideal for achieving high efficiency. As long as the DC reverse voltage is sufficiently higher than the input voltage, and the mean current flowing during the diode conduction time is within the mean output current level, and as the peak current is within the peak surge current limits, there is no problem. In this application the ROHM RB053L-30 are used. The diode mean current and diode peak current can be obtained by the following formulas.

Diode mean current : Ibi

$$I_{DI} \geq I_{O} \times (1 - \frac{V_{O}}{V_{IN}})$$

Diode peak current : Ibip

$$I_{Dip} \geq (I_{O} + \frac{V_{O}}{2L} t_{OFF})$$

Example) Using the RB053L-30

 $V_{R}$  (DC reverse voltage) = 30 V, mean output current = 3.0 A, peak surge current = 70 A,  $V_{F}$  (forward voltage) = 0.42 V, at  $I_{F}$  = 3.0 A

$$l_{\text{Di}} \geq l_{\text{O}} \times (1 - \frac{V_{\text{O}}}{V_{\text{IN}}})$$
$$\geq 3 \times (1 - 0.672)$$
$$\geq 0.984 \text{ A}$$

12.6 V output

$$I_{\text{Di}} \geq I_{\text{O}} \times (1 - \frac{V_{\text{O}}}{V_{\text{IN}}})$$
$$\geq 3 \times (1 - 0.572)$$
$$\geq 1.284 \text{ A}$$

16.8 V output

 $I_{\text{Dip}} \geq (I_{\text{O}} + \frac{V_{\text{O}}}{2L} \text{ toff})$  $\geq 3.6 \text{ A}$ 

12.6 V output

$$IDip \geq (IO + \frac{VO}{2L} tOFF)$$
$$\geq 3.6 \text{ A}$$

#### Charge current sense resistor

Please note the following in selecting the charge current sense resistance. First of all, meet the electric power to the flowing current. However, the conversion efficiency deteriorates because the loss in the sense resistance grows when resistance is adjusted to a too big value. The accuracy of the charge current deteriorates because the voltage difference of both ends of the sense resistance becomes small when resistance is adjusted to a too small value oppositely. 33 m $\Omega$  of the KOA SL1TTE33LOF is used in this application. The sense resistance value can be determined by the following formulas.

In this application, 33 m $\Omega$  of the KOA SL1TTE33LOF is used.

Sense resistor: RS2

RS2 = 
$$\frac{+INE1}{20 \times Io}$$

Example) When the +INE1 terminal (pin 9) voltage is 2 V and the charge current (Io) is 3.0 A

$$RS2 = \frac{+INE1}{20 \times Io}$$
$$= \frac{2}{20 \times 3.0}$$
$$= \frac{33.3 \text{ m}\Omega}{20 \times 3.0}$$

### • Input current sense resistor

Please note the following in selecting the input current sense resistance. First of all, meet the electric power to the flowing current. However, the conversion efficiency deteriorates because the loss in the sense resistance grows when resistance is adjusted to a too big value. The accuracy of the input current deteriorates because the voltage difference of both ends of the sense resistance becomes small when resistance is adjusted to a too small value oppositely. 33 m $\Omega$  of the KOA SL1TTE33LOF is used in this application. The sense resistance value can be determined by the following formulas.

In this application, 15 m $\Omega$  of the KOA SL1TTE15LOF is used.

Sense resistor : RS1

 $RS1 = \frac{+INE2}{20 \times I_{IN}}$ 

Example) When the +INE2 terminal (pin 3) voltage is 1.79 V and the input current (IIN) is 6.0 A

RS1	=	+INE2			
		$20  imes I_{IN}$			
	_	1.79			
	_	20×6.0			
	=	<u>14.9 mΩ</u>			

### ■ REFERENCE DATA



(Continued)





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## USAGE PRECAUTIONS

- Printed circuit board ground lines should be set up with consideration for common impedance.
- Take appropriate static electricity measures.
- Containers for semiconductor materials should have anti-static protection or be made of conductive material.
- After mounting, printed circuit boards should be stored and shipped in conductive bags or containers.
- Work platforms, tools, and instruments should be properly grounded.
- Working personnel should be grounded with resistance of 250 k $\Omega$  to 1 M $\Omega$  between body and ground.
- Do not apply negative voltages.
- $\bullet$  The use of negative voltages below –0.3 V may create parasitic transistors on LSI lines, which can cause abnormal operation.

### ORDERING INFORMATION

Part number	Package	Remarks
MB39A125PFV	24-pin plastic SSOP (FPT-24P-M03)	
MB39A125WQN	28-pin plastic QFN (LCC-28P-M11)	
MB39A126PFV	24-pin plastic SSOP (FPT-24P-M03)	
MB39A126WQN	28-pin plastic QFN (LCC-28P-M11)	

### PACKAGE DIMENSIONS



(Continued)



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